

WSP6077

**Dual P-Ch MOSFET** 

#### **General Description**

The WSP6077 is the highest performance trench P-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSP6077 meet the RoHS and Green Product requirement with full function reliability approved.

#### Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

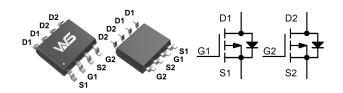
### **Product Summery**

BVDSS	RDSON	ID
-60V	60mΩ	-8A

#### Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

#### **SOP8 Pin Configuration**



Symbol	Parameter	Rating	Units	
V <sub>DS</sub>	Drain-Source Voltage	-60	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$ -8.0		A	
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, -V <sub>GS</sub> @ -10V <sup>1</sup>	-4.5	A	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup> -30		А	
P <sub>D</sub> @T <sub>C</sub> =25℃	Total Power Dissipation <sup>3</sup> 1.5		W	
T <sub>STG</sub>	Storage Temperature Range	ange -55 to 150		
TJ	Operating Junction Temperature Range -55 to 150		°C	

## Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R <sub>eja</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>		70	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>		35	°C/W

#### **Absolute Maximum Ratings**



WSP6077

**Dual P-Ch MOSFET** 

#### Electrical Characteristics (T<sub>J</sub>=25<sup>-1</sup>C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-60			V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$ , I_D=-1mA		-0.02		V/℃
Б	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-5A		60	80	mΩ
R <sub>DS(ON)</sub>		V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-2A		64	100	
V <sub>GS(th)</sub>	Gate Threshold Voltage		-1.0	-1.5	-2.5	V
	V <sub>GS(th)</sub> Temperature Coefficient	$V_{GS} = V_{DS}$ , $I_D = -2500A$		4.32		mV/°C
	Drain-Source Leakage Current	$V_{DS}$ =-52V , $V_{GS}$ =0V , $T_{J}$ =25 $^{\circ}$ C			-1	
I <sub>DSS</sub>		$V_{DS}$ =-52V , $V_{GS}$ =0V , $T_{J}$ =55 $^{\circ}$ C			-5	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm20V$ , $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-5A		15		S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		13	30	Ω
Qg	Total Gate Charge (-4.5V)			10		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-30V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-5A		3.2		
Q <sub>gd</sub>	Gate-Drain Charge			2.5		
T <sub>d(on)</sub>	Turn-On Delay Time			21		
Tr	Rise Time	V <sub>DD</sub> =-30V , V <sub>GS</sub> =-10V ,		19		
T <sub>d(off)</sub>	Turn-Off Delay Time	R <sub>G</sub> =3.3Ω I <sub>D</sub> =-1A		55		ns -
T <sub>f</sub>	Fall Time			7.0		
Ciss	Input Capacitance			1400		
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-30V , V <sub>GS</sub> =0V , f=1MHz		95		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			70		

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,4</sup>	$-V_G=V_D=0V$ , Force Current			-8	А
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>				-30	А
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25℃			-1.2	V

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec.

2.The data tested by pulsed , pulse width  $\leq$  300us , duty cycle  $\leq$  2%

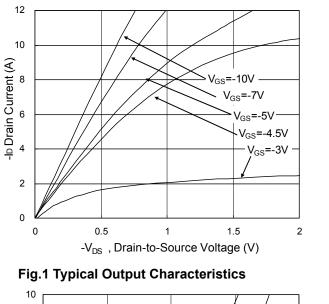
3.The power dissipation is limited by 150  $^\circ\!\!\mathbb{C}$  junction temperature

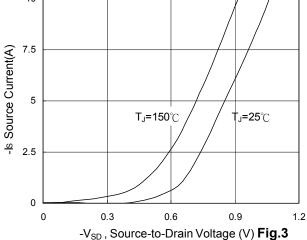
4. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



WSP6077 Dual P-Ch MOSFET

# **Typical Characteristics**







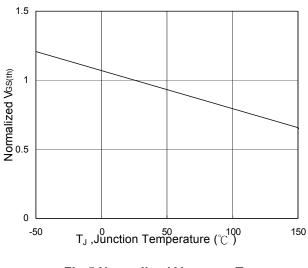


Fig.5 Normalized  $V_{GS(th)}$  vs. T<sub>J</sub>

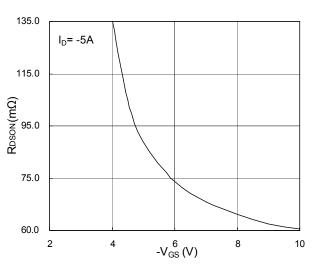
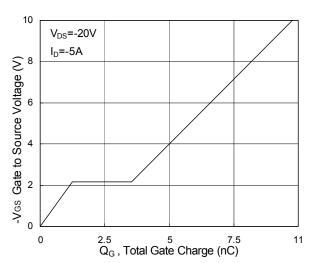
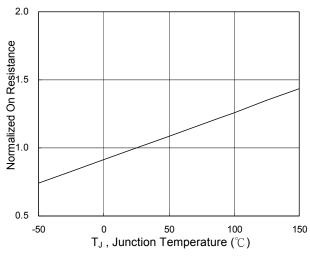
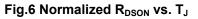


Fig.2 On-Resistance vs. G-S Voltage









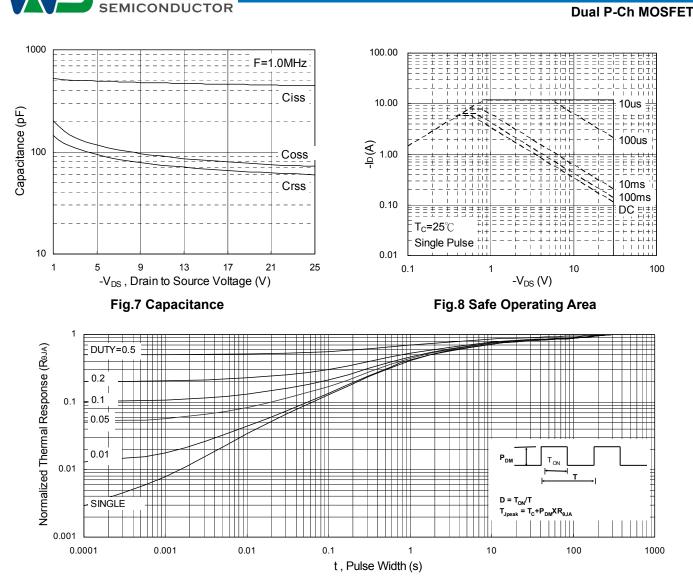
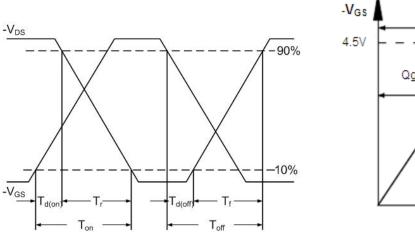


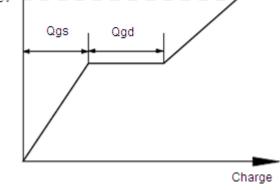
Fig.9 Normalized Maximum Transient Thermal Impedance





Wil

NSOK



Qg



**WSP6077** 



# Attention

1, Any and all Winsok power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your Winsok power representative nearest you before using any Winsok power products described or contained herein in such applications.

2, Winsok power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all Winsok power products described or contained herein.

3, Specifications of any and all Winsok power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, Winsok power Semiconductor CO., LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.

5, In the event that any or all Winsok power products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

6, No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of Winsok power Semiconductor CO., LTD.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. Winsok power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the Winsok power product that you Intend to use.

9, this catalog provides information as of Sep.2014. Specifications and information herein are subject to change without notice.

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Winsok manufacturer:

Other Similar products are found below :

IRFD120 JANTX2N5237 2SK2267(Q) BUK455-60A/B TK100A10N1,S4X(S MIC4420CM-TR VN1206L NDP4060 SI4482DY IRS2092STRPBF-EL IPS70R2K0CEAKMA1 TK31J60W5,S1VQ(O TK31J60W,S1VQ(O TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1 DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1 MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1\_T0\_00201 PJMF380N65E1\_T0\_00201 PJMF280N60E1\_T0\_00201 PJMF600N65E1\_T0\_00201 PJMF900N65E1\_T0\_00201